Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	24	US-6222722-$.DID. OR US-6204070-$.DID. OR US-6207487-$.DID. OR US-6391803-$.DID. OR US-6420230-$.DID. OR US-6281543-$.DID. OR US-5452178-$.DID. OR US-0645416-$.DID. OR US-6309923-$.DID. OR US-6270572-$.DID. OR US-6551399-$.DID. OR US-6780704-$.DID.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 13:15
L2	3	1 and(nitride adj layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 13:18
L3	0	1 and(rough adj silicon adj layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 13:19
L4	2	"20020109198"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 13:19
L5	0	4 and(rough adj silicon adj layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 13:22
L6	11	capacitor.ti. and(rough adj silicon adj layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 13:25
L7	1769	memory adj device.ti. and(storage adj node)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 13:28

L8	1283	7 and(capacitor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 13:28
L9	0	8 and(rough adj silicon adj nitride)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 13:29
L10	353	8 and(silicon adj nitride)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 13:30
L11	0	8 and(rough adj silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 13:29
L12	353	10 and(memory adj device)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 13:30
L13	12	12 and(microprocessor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 14:42
L14	1	13 and(nitride adj layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 13:53
L15	1548	capacitor.ti. and(silicon adj nitride adj layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 14:46

L16	1255	15 and(electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 14:59
L17	1194	16 and(dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 15:10
L18	630	17 and(memory adj cell)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 15:11
L19	573	18 and(DRAM)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 15:11
L20	41	19 and(microprocessor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 15:12